

Title (en)

METHOD FOR PRODUCING A SEMICONDUCTOR LAYER SEQUENCE, RADIATION-EMITTING SEMICONDUCTOR CHIP, AN OPTOELECTRONIC COMPONENT

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER HALBLEITERSCHICHTENFOLGE, STRALUNGSEMITTIERENDER HALBLEITERCHIP UND OPTOELEKTRONISCHES BAUTEIL

Title (fr)

PROCÉDÉ DE FABRICATION D'UNE SUCCESSION DE COUCHES SEMI-CONDUCTRICES, PUCE DE SEMI-CONDUCTEUR ÉMETTANT UN RAYONNEMENT, ET COMPOSANT OPTOÉLECTRONIQUE

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Application

EP 11763943 A 20110930

Priority

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Abstract (en)

[origin: WO2012049031A1] The invention relates to a method for producing a semiconductor layer sequence, which is based on a nitride compound semiconductor material and which comprises a microstructured outer surface, to a semiconductor chip produced using said method, and to an optoelectronic component comprising such a semiconductor chip. The method has the following steps: A) growing at least one first semiconductor layer of the semiconductor layer sequence on a substrate; B) applying an etch-resistant layer on the first semiconductor layer; C) growing at least one further semiconductor layer on the layer sequence obtained in step B); D) separating the semiconductor layer sequence from the substrate, a separating zone of the semiconductor layer sequence being at least partly removed; E) etching the obtained separating surface of the semiconductor layer sequence by means of an etching means such that a microstructuring of the first semiconductor layer is carried out and the microstructured outer surface is formed.

IPC 8 full level

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